Roll No.

Total No of Pages: 3

#### 7E7081

B. Tech. VII Sem. (Main/Back) Exam., Nov.-Dec. - 2017 **Electronics & Communication Engineering 7EC1A Antenna & Wave Propagation** 

**Time: 3 Hours Maximum Marks: 80** Min. Passing Marks: 26

Instructions to Candidates:

Attempt any five questions, selecting one question from each unit. All questions carry equal marks. Schematic diagrams must be shown wherever necessary. Any data you feel missing suitably be assumed and stated clearly.

*Units of quantities used/calculated must be stated clearly.* 

Use of following supporting material is permitted during examination. (Mentioned in form No. 205)

1. Graph Table

## **UNIT-I**

- Derive an expression of radiated power and radiation resistance of a Hertzian dipole. [8]
  - Define Reciprocity and antenna temperature. [4]
  - Find the radiation resistance of a Hertzian dipole of length  $\frac{\lambda}{40}$  and  $\frac{\lambda}{60}$ [4] (c)

## OR

- What is the effective area of a half wave dipole operating at 500 Mhz? [4] Q.1 (a)
  - Briefly define the types of polarization... [4] (b)
  - Find the directivity of a current element Idl. [8] (c)

[4640] Page 1 of 3 [7E7081]

# <u>UNIT-II</u>

Q.2	(a)	What is multiplication of patterns? Explain with suitable examples.	[8]
	(b)	An array contains 100 isotropic radiators with an inter element spacing	g of 0.5λ. It
		is required to produce broadside and end fire beams.	[8]
		(i) Find Null to Null beam width and half power width in degrees	
		(ii) Find the directivity of both forms of arrays	* * *
		<u>OR</u>	4 * 4 4
Q.2	(a)	A uniform lineary array is required to produce an end fire beams	when it is
		operated at a frequency of 10 Ghz. It contains 50 radiators and are space	ed at 0.5λ.
		Find the progressive shift required to produce the end fire beam. Fin	d the array
		length.	[8]
	(b)	Calculate the field strength of a uniform linear array.	[8]
17		<u>UNIT-III</u>	
Q.3	(a)	Briefly explain reflector antennas and micro strip patch antenna.	[12]
Ô	(b)	Explain the method of Antenna radiation patterns measurements.	[4]
		<u>OR</u>	
Q.3	(a)	Discuss the characteristics and operation V and Rhombic antennas.	[10]
	(b)	Design a three element Yagi-Uda antenna to operate at a fre	quency of
•	•	172 Mhz.	[6]
		<u>UNIT-IV</u>	
Q.4	(a)	Derive an expression of field strength due to space wave.	[8]
	(b)	What are the factors for affecting space wave field strength?	[8]
[7E7	081]	Page 2 of 3	[4640]

		OR
Q.4	(a)	Explain the following in brief: [8]
		(i) Duct propagation
		(ii) Trope scatter
	(b)	Derive an expression for radio horizon distance in kilometers [5]
	(c)	Find the radio horizon distance of a transmitting antenna whose height
	6	is 80 m.
		<u>UNIT-V</u>
Q.5	(a)	Discuss the characteristics of different Ionosphere layers in brief. [8]
	(b)	Determine the critical frequency of EM wave for DCN = 400 electrons/cm <sup>3</sup> ),
	•	E $(5\times10^8 \text{ electrons/cm}^3)$ and F $(2\times10^6 \text{ electrons/cm}^3)$ layers. [8]
		<u>OR</u>
Q.5	(a)	Explain the following characteristic parameters of Ionosphere propagation. [12]
		(i) Critical frequency
		(ii) Maximum usable frequency, Muf
		(iii) Skip distance
		(iv) Virtual height
	(b)	An HF radio communication is to be established between two points on the

[7E7081]

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ionosphere layer is 200 km and critical frequency is 4? MHz. find MUF.

earth's surface. The points are at a distance of 2600km. The height of the

[4640]

[4]

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#### 7E7072

B. Tech. VII Sem. (Main/Back) Exam, Nov- Dec. 2017 Applied Electronics Instrumentation & Engineering 7AI2A Digital Signal Processing AI, EC, EIC

**Time: 3 Hours** 

Maximum Marks: 80 Min. Passing Marks: 26

Instructions to Candidates:

Attempt any five questions, selecting one question from each unit. All questions carry equal marks. Schematic diagrams must be shown wherever necessary. Any data you feel missing suitably be assumed and stated clearly.

Units of quantities used/calculated must be stated clearly.

Use of following supporting material is permitted during examination. (Mentioned in form No. 205)

1. <u>NIL</u>

2. NIL

## **UNIT-I**

- Q.1 (a) State Shannon's sampling theorem. Explain sampling with zero order hold and reconstruction of signals. [8]
  - (b) The signal  $x_c(t) = \sin \left[2\pi(100)t\right]$  was sampled with sampling period T = 1/400 second to obtain a discrete time signal x[n]. What is the resulting signal x[n].

#### <u>OR</u>

- Q.1 (a) Define Aliasing with suitable waveform. Explain its effect and how it can be prevented. [8]
  - (b) Let x(t) be a band limited signal such that X(jw) = 0 for |w| ≥ π/T [8]
     If x(t) is sampled using a sampling period T, determine an interpolating function g(t) such that

$$\frac{dx(t)}{dt} = \sum_{n=-\infty}^{\infty} x(nT) \quad g(t-nT)$$

[7E7072]

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[4620]

## **UNIT-II**

Discuss Minimum phase system with example. Q.2 (a) [8] Check whether the following systems are linear: (b) [8] (i) F[x(n)] = an x(n) + b $F[x(n)] = e^{x(n)}$ OR Explain the condition for an LTI discrete time system to be causal. Q.2 (a) [6] (b) Check whether the discrete time system represented by following equations are Linear and causal - $[5 \times 2 = 10]$  $y(n) = 3y^{2}(n-1) - n x(n) + 4x(n-1) - 2x(n+1)$  $y(n) = x(n + 1) - 3x(n) + x(n - 1) ; n \ge 0$ **UNIT-III** Determine the direct form I and II realizations for a IIIrd Order IIR transfer Q.3 (a) function. [8] H (z) =  $\frac{0.28z^2 + 0.319z + 0.04}{0.5z^3 + 0.3z^2 + 0.17z - 0.2}$ Explain cascade and parallel realization of IIR systems with example. [8] OR Q.3 Draw the structures of cascade & parallel realization of [16] H(z) =  $\frac{(1-z^{-1})^3}{(1-\frac{1}{2}z^{-1})(1-\frac{1}{8}z^{-1})}$ 

## **UNIT-IV**

Q.4 (a) Apply bilinear transformation to [8]  $H(s) = \frac{2}{(s+1)(s+3)}$ With T = 0.1s. Describe Chebyshev filters with its response. (b) [8] Convert the analog filter into a digital filter whose system function is [8]  $H(s) = \frac{s + 0.2}{(s + 0.2)^2 + 9}$ Use the impulse invariant technique. Assume T = ls. Discuss FIR filters by windowing technique. Give the filter response of all window functions. [8] **UNIT-V** List out the properties of Discrete Fourier Transform (DFT). [8] (b) Find the N point DFT for  $x(n) = a^n$  for 0 < a < 1[8] <u>OR</u> Find the inverse DFT of  $X(k) = \{1, 2, 3, 4\}$ Q.5 (a) [10] Explain DIT (Decimation - In - time) algorithm. [6]

Total No of Pages: 3 Roll No. **7E7078** B. Tech. VII Sem. (Main/Back) Exam., Nov- Dec. 2017 **Electronic Instrumentation & Control Engineering 7EI3A Digital Image Processing** EC, EIC **Maximum Marks: 80** Time: 3 Hours Min. Passing Marks: 26 Instructions to Candidates: Attempt any five questions, selecting one question from each unit. All questions carry equal marks. Schematic diagrams must be shown wherever necessary. Any data you feel missing suitably be assumed and stated clearly. Units of quantities used/calculated must be stated clearly. Use of following supporting material is permitted during examination. (Mentioned in form No. 205) 2. NIL 1. NIL **UNIT-I** [8] Q.1 (a) Explain zooming and shrinking of digital images. What is color model or color system? Explain RGB and CMY and HSI color [8] model. OR Q.1 Explain various fundamental step in DIP with neat block diagram and also write [16] applications of digital Image Processing. **UNIT-II** Q.2 (a) Explain spatial filtering. Define spatial correlation and convolution with an [8] example. (b) Explain first and second order derivatives of image sharpening. [8]

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[7E7078]

[3740]

## <u>OR</u>

Q.2	(a)	Explain the intensity transformation function.		[8]
	(b)	Describe the various types of image smoothing u	ising frequency	domain
		filters.		[8]
		<u>UNIT-III</u>		
Q.3	(a)	Explain Inverse filtering and Wiener filtering.	*	[8]
	(b)	Explain noise probability density functions.		[8]
		<u>OR</u>		
Q.3	(a)	What is digital image degradation model? Explain noise	models.	[16]
		<u>UNIT-IV</u>		
Q.4	(a)	Explain morphological reconstruction and smoothing.		[8]
	(b)	What is the difference between erosion and dilation?		[8]
		<u>OR</u>		
Q.4	Writ	te a short notes:	*	[16]
	(a)	Convex Hull		
	(b)	Thinning		
	(c)·	Pruning		
	(d)	Skeletons		
		50,700 62		

# <u>UNIT-V</u>

35%

Q.5	Exp	lain Lossy Compression techniques.	[16]
		<u>OR</u>	
Q.5	Wri	te short notes on:	[16]
	(a)	Lossy predictive coding;	
	(b)	Lossless predictive coding and compare both.	

7E7083

Roll No. \_\_\_\_

Total No of Pages: 3

7E7083

B. Tech. VII Sem. (Main/Back) Exam., Nov- Dec. 2017 Electronics & Communication Engineering 7EC4A Wireless Communication

**Maximum Marks: 80 Time: 3 Hours** Min. Passing Marks: 26 Instructions to Candidates: Attempt any five questions, selecting one question from each unit. All questions carry equal marks. Schematic diagrams must be shown wherever necessary. Any data you feel missing suitably be assumed and stated clearly. Units of quantities used/calculated must be stated clearly. Use of following supporting material is permitted during examination: (Mentioned in form No. 205) 2.- NIL 1. NIL **UNIT-I** Q.1 (a) Explain FHSS with basic block diagram and find the expression for processing [12] gain (Gp) in fast and slow system. (b) How CDM is better than TDM and FDM? [4] OR Q.1 (a) Explain the working of DSSS with the help of binary phase shift keying. [8] What do you mean by code division multiplexing? [8] **UNIT-II** Q.2 Define the following terms for a digital wireless cellular system- $[4 \times 4 = 16]$ CIR (a) Spectral efficiency (b) (c) First Fresnel Zone (d) Path loss

[7E7083]

Page 1 of 3

[4060]

# <u>OR</u>

Q.2 (a) What is link engineering? Explain different types of link used in commun			ion
		system.	[8]
	(b)	What is multipath fading? Explain various fading channels present.	[8]
		<u>UNIT-III</u>	
Q.3	(a)	Explain the TDMA principle of operation with TDMA/TDD example and a	lso
		The state of the s	[8]
26.5	(b)	Explain following terms-	[-]
		(i) CDMA power control	
		(ii) Handoff [2×4=	=81
		<u>OR</u>	
Q.3	(a)	The "Near-For interference" is a serious problem in a wireless cellular CDM	ΛA
		notwoods Emplain the agent Cal	[4]
	(b)	Compare FDMA, TDMA and CDMA.	12]
		<u>UNIT-IV</u>	
Q.4	(a)	Explain the operation of DECT with its network architecture.	[8]
	(b)	What is the mineral of C	[4]
	(c)	What is the difference by	[4]
		OR	נידן
Q.4	(a)	Write short note on- (Any two) [2×8=]	61
		(i) Wi–Fi	.oj
		(ii) Zigbee	
		(iii) Mobile IP	
		(iv) Bluetooth	
		(v) RFID Technology	
		sy zoomotogj	
[7E7	083]	Page 2 of 3	

## **UNIT-V**

Q.5 (a) Explain following terms- $[2 \times 4 = 8]$ Orbital period (i) (ii) Orbital velocity (iii) Coverage angle (iv) Slant range (b) Explain earth station antennas. [8] <u>OR</u> Q.5 Write short note on- $[4 \times 4 = 16]$ (i). Low noise amplifier (ii) High power amplifier (iii) Up converter (iv) AOCS and TTC

Roll No. Total No of Pages: 3 **7E7084** B. Tech. VII Sem. (Main/Back) Exam., Nov- Dec.2017 **Electronics & Communication Engineering 7EC5A VLSI Design Time: 3 Hours Maximum Marks: 80** Min. Passing Marks: 26 Instructions to Candidates: Attempt any five questions, selecting one question from each unit. All questions carry equal marks. Schematic diagrams must be shown wherever necessary. Any data you feel missing suitably be assumed and stated clearly. Units of quantities used/calculated must be stated clearly. Use of following supporting material is permitted during examination. (Mentioned in form No. 205) 1. NIL · **UNIT-I** [8] Q.1 (a) Explain the NMOS fabrication process with suitable diagrams. (b) An enhancement type NMOS transistor with  $V_t = 0.7V$  conducts  $I_D 100 \mu A$  when  $V_{GS} = V_{DS} = 1.2V$ . Find the value of  $I_D$  for  $V_{GS}$  1.5V and  $V_{DS}$  3V. Also calculate the value of drain to source resistance  $r_{ds}$  for small  $V_{DS} = V_{GS} = 3.2V.$ [8] OR Q.1 (a) Find the relationship between drain to current source  $(I_{ds})$  to voltage  $(V_{ds})$  in non -saturated region. [8] (b) What are various second order effect? Discuss how many have been included

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[8]

[4100]

into device model of MOS transistor?

[7E7084]

# <u>UNIT-II</u>

Q.2 (a	a)	Determination of pull up to pull down ratio [Z <sub>Pu</sub> /Z <sub>pd</sub> ] for NMOS inverter of	driver
		by another NMOS inverter.	[8]
(t	b)	Design the following logics using CMOS:	
		(i) $Y = ABC + \overline{ABC}$	[4]
		(ii) $Y = AB\overline{C} + \overline{A}BC$	[4]
		OR :	
Q.2 (a	a)	Describe the structure of CMOS transmission gate. Explain why such a g	ate is
		desirable to control transmission of signal rather than single transistor?	[8]
(b	)	What is noise margin? Explain the procedure to determine noise margin?	[8]
		<u>UNIT-III</u>	
Q.3 (a	1)	Draw the stick diagram layout for -	
		(i) 2 input CMOS NAND gate	[4]
		(ii) 2 input CMOS NOR gate	[4]
(b	)	Explain the layout design rules.	[8]
		<u>OR</u>	
Q.3 (a)	)	Explain the layout for NAND gate with suitable example.	[8]
(b)	)	Find the network graph and common Euler path for PMOS and NMOS net	
		in the given function $F = \overline{A + BC}$	[8]
7E <b>7</b> 084	4]	Page 2 of 3 [410	0]

# UNIT-IV

Q.4	(a) Co	ompare the SRAM and DI	RAM cell.				[8]
	(b) Ex	plain various types of me	emories.				[8]
			<u>OR</u>				
Q.4	(a) De	fine clocked CMOS logic	and its advant	ages.			[8]
	(b) Bri	iefly explain NORA and l	NP (zipper) log	ic.			[8]
			UNIT-V				[0]
Q.5 (	(a) Wr	ite a VHDL code for-			8		
	(i)	J. K flip flop					[4]
	(ii)	T flip flop					[4]
(	b) Exp	plain the ECAD tools for	first back desig	n.			[8]
			<u>OR</u>			- ;	[0]
Q.5 (a	a) Wri	te short note on:					
	(i)	Behavioral Modelling	a.				[4]
	(ii)	Structural Modelling					[4]
(t	b) Wri	te a VHDL code for struc	tural modelling	of full Adder			[8]
							7.00

Roll No. Total No of Pages: 3 7E7085 B. Tech. VII Sem. (Main/Back) Exam., Nov- Dec.2017 **Electronic Instrumentation & Control Engineering 7EI6.2A Advanced Microprocessor** EC, EIC Time: 3 Hours **Maximum Marks: 80** Min. Passing Marks: 26 Instructions to Candidates: Attempt any five questions, selecting one question from each unit. All questions carry equal marks. Schematic diagrams must be shown wherever necessary. Any data you feel missing suitably be assumed and stated clearly. *Units of quantities used/calculated must be stated clearly.* Use of following supporting material is permitted during examination. (Mentioned in form No. 205) 1. NIL **UNIT-I** Draw and explain Read and Write cycle timing diagram of 8086. [8] (b) Explain Addressing Modes of 8086 Microprocessor. [8] OR Q.1 Draw internal Architecture of 8086. Explain the function of various registers. [16] **UNIT-II** What is the difference between Macros and Subroutines? Explain Q.2 (a) [8] with examples. (b) What is strings, Explain with example. [8] [1440] [7E7085]. Page 1 of 3

## <u>OR</u>

Q.2	2 (a)	Explain Assembler Directives and Operators.	[8]
,	(b)	Explain classification of interrupts.	[8]
		<u>UNIT-III</u>	
Q.3	Exp	plain various programming modes of 8279 keyboard and displa	y controller. Also
	dra	w a block diagram showing its interfacing with Microprocessor.	[16]
		<u>OR</u>	
Q.3	Wr	ite short note on- (Any two)	[8×2=16]
	(a)	RS – 232	
	(b)	IEEE 488	
	(c)	8086 based process control system.	, .a.
		<u>UNIT-IV</u>	
Q.4	(a)	Draw the interfacing diagram of 8257 DMA controller	and Explain its
		operation.	[10]
	(b)	Compare static memory and dynamic memory.	[6]
		<u>OR</u>	,
Q.4	(a)	What are I/O ports? What are programmable and non- programm	able ports? [8]
	(b)	What is memory interfacing and decoding?	[8]
[7E70	085]	Page 2 of 3	[1440]

# **UNIT-V**

Q.5	Exp	lain the architecture of following processors.	[8×2=16]	
	(a)	80286		
	(b)	80486		
		<u>OR</u>		
Q.5	(a)	Explain the concept of multiuser/ multi tasking operating system.	[10]	
	(b)	Explain Register organization of 80386.	[6]	

Total No of Pages: 4 Roll No. **7E7086** B. Tech. VII Sem. (Main/Back) Exam., Nov - Dec. 2017 **Electronics & Communication Engineering** 7EC6.3A VHDL **Maximum Marks: 80** Time: 3 Hours Min. Passing Marks: 26 Instructions to Candidates: Attempt any five questions, selecting one question from each unit. All questions carry equal marks. Schematic diagrams must be shown wherever necessary. Any data you feel missing suitably be assumed and stated clearly. Units of quantities:used/calculated must be stated clearly. Use of following supporting material is permitted during examination. (Mentioned in form No. 205) 1. NIL **UNIT-I** [6] Differentiate between synthesis and simulation process in VHDL. (b) List the advantages of VHDL for digital design over the traditional methods. [4] Describe Design flow of ASICs. (c) OR Assume that a gate array exists in which the logic cell used is a three inputs NOR Q.1 (a) gate. The inputs to each NOR gate can be connected to either 1 or 0, or to any logic signal. Show how the following logic functions can be realized in the gate [12]array. (Use Demorgan's theorem). (i)  $f_1 = (x_1 + x_3)(x_2 + \overline{x}_3)$ (ii)  $f_2 = (x_2 + \overline{x}_3)(x_1 + \overline{x}_2 + x_3)$ Describe History of various Hardware Description Languages in brief manner. [4]

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[7E7086]

[3000]

## **UNIT-II**

Consider the following VHDL assignment statements [12]  $F_1 < = ((x_1 \text{ and } x_3) \text{ or (not } x_1 \text{ and not } x_3))$ and  $((x_2 \text{ and } x_4) \text{ or (not } x_2 \text{ and not } x_4));$  $F_2 < = (x_1 \text{ and } x_2 \text{ and not } x_3 \text{ and not } x_4) \text{ or }$ (not  $x_1$  and not  $x_2$  and  $x_3$  and  $x_4$ ) or  $(x_1 \text{ and not } x_2 \text{ and not } x_3 \text{ and } x_4) \text{ or (not } x_1 \text{ and } x_2 \text{ and } x_3 \text{ and not } x_4);$ Write complete VHDL code to implement f1 & f2. (i) (ii) Draw its timing simulation waveforms. What is the difference between signals and data types? Mention in tabulation form. [4] OR Q.2 (a) What do you mean by architectures and RTL schematics? (i) [3] Explain different types of architectures with examples. (ii) [3] (iii) What are sizes of entity and architecture which is defined in VHDL coding? [2] Write short notes on any two:  $[2 \times 4 = 8]$ (i) Packages Simulation approaches (iii) Elaboration signal drivers simulator kernel process [7E7086] Page 2 of 4 [3000]

## **UNIT-III**

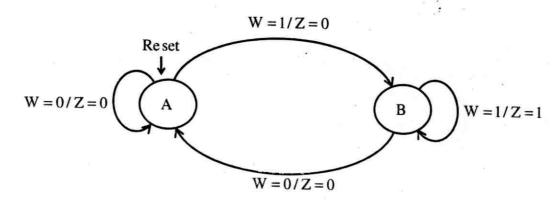
- Q.3 (a) Write VHDL code that represents a BCD to 7-segment decoder. Also draw its timing simulation waveforms. [8]
  - (b) Describe multiplexer synthesis using Shannon's expansions by explaining implementation of the three input majority function using a 4 to 1 multiplexer. [8]

## <u>OR</u>

- Q.3 (a) Write VHDL code for implementing D flip-flop using a WAIT-UNTIL statement. [8]
  - (b) What do you mean by counters? How many types of counters are there? Write their name. Write VHDL code for a down counter. [6]
  - (c) Define n bit shift register. [2]

## UNIT-IV

Q.4 (a) Write VHDL code for given state diagram of mealy type finite state machine. [8]



- (b) Tabulate comparisons between synchronous and Asynchronous sequential circuits.
- (c) Define state diagram and state table. [2]

[7E7086] Page 3 of 4 [3000]

## <u>OR</u>

Q.4	(a)	What are the differences between Mealy and Moore Machines? Mention	n in
		tabular form.	[4]
	(b)	What do you mean by vending machine controller? Explain its working	and
		specifications.	[4]
	(c)	Write VHDL code for Moore type FSM.	[8]
		. <u>UNIT-V</u>	
Q.5	(a)	Write VHDL code for a n- bit register with an enable input.	[12]
	(b)	Explain and draw data path circuit for the multiplier.	[4]
		<u>OR</u>	
Q.5	(a)	Explain clock synchronization using tristate buffers in the data path circuit.	[8]
	(b)	Describe CPU organization and also explain its design concepts.	[8]
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Total No of Pages: 3 Roll No. 7E4047 B. Tech. VII Sem. (Back) Exam., Nov. - Dec. - 2017 **Electronics & Communication Engineering** 7EC4 (O) IC Technology **Maximum Marks: 80 Time: 3 Hours** Min. Passing Marks: 26 Instructions to Candidates: Attempt any five questions, selecting one question from each unit. All questions · carry equal marks. Schematic diagrams must be shown wherever necessary. Any data you feel missing suitably be assumed and stated clearly. 'Units of quantities used/calculated must be stated clearly. Use of following supporting material is permitted during examination. (Mentioned in form No. 205) · 2. NIL 1. **NIL** UNIT-I [8] Explain different kind of Crystal defects. Q.1 (a) What is float zone growth? What are different kinds of doping for float zone (b) [8] growth? OR Q.1 (a) What is chemical etching and polishing? Explain the need of chemical [8] cleaning. (b) Find the concentration of boron in crystal at 0.5 fraction solidified, if C<sub>S</sub> at X = 0.04 is  $2 \times 10^{18}$  and segregation coefficient = 0.8. [8]

# <u>UNIT-II</u>

Q.2	(a)	Explain the electric field effect on diffusion. What is the maximu	m value of
		electric field enhancement factor?	[8]
	(b)	What do you understand by diffusion in SiO <sub>2</sub> ? What are the basic tec	hniques for
		measuring the diffusivity?	[8]
		<u>OR</u>	
Q.2	(a)	Explain the utility of ion-implantation for shallow junctions.	[8]
	(b)	Explain the need of pre oxidation clearing before oxidation.	[8]
		<u>UNIT-III</u>	
Q.3	Exp	plain the chemical vapour deposition technique of silicon dioxide in detail	il. [16]
		<u>OR</u>	
Q.3	Wha	at are the different defects in epitaxial growth? How the slips are product	duced from
	epita	axial defects?	[16]
		<u>UNIT-IV</u>	
Q.4	(a)	Discuss the various parameters of performance of photolithography.	[8]
	(b)	What is projection printer? Give the following values related to	projection
		printers:	[8]
y	*	(i) Resolution	
		(ii) Depth of focus	
		(iii) Spatial frequency	
[7E4	047]	Page 2 of 3	[1220]

## <u>OR</u>

Q.4	Wri	ite technical note on following:	
	(a)	Wet etching	[8]
	(b)	Plasma etching	[8]
		<u>UNIT-V</u>	
Q.5	(a)	Compare CMOS & NMOS IC technology	[8]
	(b)	What are basic fundamental considerations for IC processing?	
		<u>OR</u> ∴	
Q.5	Exp	lain any two:	[8+8=16]
	(a)	Bipolar IC technology	1
	(b)	Trench Isolation	
	(c)	Metallization	
		a n	[ 2 <sup>n</sup> ]

=	Roll No	Total No of Pages: 3
48	7E404	8
7E4048	B. Tech. VII Sem. (Back) Exa Electronics & Communic 7EC5 (O) VLS	cation Engineering
Time: 3	Hours	Maximum Marks: 80 Min. Passing Marks: 26
	ons to Candidates:	
	mpt any five questions, selecting one que	
	ry <b>equal</b> marks. Schematic diagrams must	
	a you feel missing suitably be assumed and its of quantities used/calculated must be st	- 1 - 1
	e of following supporting material is	
	entioned in form No. 205)	
1. NIL	2 - 1 - 1 - 1 - 1 - 1 - 1 - 1 - 1 - 1 -	2. NIL
	<u>UNIT-I</u>	
Q.1 (a)	What is basic MOS transistor? Explain st	tructure and operation of basic MOS
	transistor.	[8]
(b)	Derive the V - I characteristics of enhance	ement MOSFET in ohmic region and
	saturation region.	[8]
9	<u>OR</u>	
Q.1 (a)	Draw & explain various steps involved in r	nwell CMOS fabrication. [8]
(b)	How an NMOS transistor is fabricated?	Explain the basic steps of NMOS
	fabrication in detail.	[8]

Page 1 of 3

[7E4048]

[1420]

## <u>UNIT-II</u>

Q.2	(a)	What is channel length modulation? How the $V-I$ characteristics modify with
		channel length modulation.effect? [8]
	(b)	Draw MOS transistor circuit model. [8]
		<u>OR</u>
Q.2	(a)	Write short note on Aspect of Threshold Voltage. [8]
	(b)	Draw and explain Voltage Transfer Characteristic (VTC) of CMOS Inverter. [8]
		<u>UNIT-III</u>
Q.3	(a)	What is CMOS transmission gate? Draw two input multiplexer circuit using
		it. [8]
3.	(b)	Derive the expression of propagation delay in CMOS Inverter. [8]
		<u>OR</u>
Q.3	(a)	Explain CMOS logic and draw the circuit diagram for logic function
		$Y = \overline{(D+E+A)(B+C)} \text{ using CMOS.} $ [8]
	(b)	What is noise margin? Explain the procedure to determine noise margin. [8]
		<u>UNIT-IV</u>
Q.4	(a)	Write short note on layout optimization. [8]
	(b)	Draw the transistor level diagram and layout of CMOS Inverter. [8]
		<u>OR</u>
Q.4	(a)	Draw layout of Two Input CMOS NAND and NOR gate. [8]
	(b)	Why scaling has a great importance in VLSI circuits? Explain Briefly. [8]
[7E4	1048]	Page 2 of 3 [1420]

# <u>UNIT-V</u>

Q.5	(a)	Write VHDL code of Half -	adder by following mode	eling style:	
		(i) Data flow			[4]
		(ii) Behavioral		2	[4]
		(iii) Structural			[4]
	(b)	Differentiate signal and varia	able in VHDL.		[4]
Q.5	Defi	ine the following in VHDL:	<u>OR</u>		
	(a)	Entity		•	[4]
	(b)	Architecture			[4]
	(c)	Package		*	[4]
	(d)	Configuration			[4]
		W		ħ	

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Roll No.

Total No of Pages: 3

## 7E4051

B. Tech. VII Sem. (Back) Exam., Nov. - Dec. - 2017 **Electronics & Communication Engineering** 7EC6.3 (O) Operating System

**Maximum Marks: 80** Time: 3 Hours Min. Passing Marks: 26 Instructions to Candidates: Attempt any five questions, selecting one question from each unit. All questions carry equal marks. Schematic diagrams must be shown wherever necessary. Any data you feel missing suitably be assumed and stated clearly. Units of quantities used/calculated must be stated clearly. Use of following supporting material is permitted during examination. (Mentioned in form No. 205) 2. NIL 1. NIL **UNIT-I** Q.1 (a) What is operating system? Explain the various types of operating system. [8] How does the window handle various operating system services? Explain. [8] OR Q.1 (a) Why is Linux a preferred choice in big-companies? What is frame work? [6] [6] Explain time shared and real time system. (b) [4] Define system calls. (c) **UNIT-II** Q.2 (a) Explain state transition diagram of process and also explain Process Control [8] Block (PCB). Write short notes on:-[4]

[7E4051]

(i)

(ii)

Semaphores

Monitor

Page 1 of 3

[1140]

[4]

## <u>OR</u>

Q.2	(a)	Which CPU scheduling method will give the minimum average waiting	g time?
		What is the main difficulty in its implementation?	[8]
	(b)	What is difference between preemptive and non-preemptive scheduling?	[4]
	(c)	Explain the turnaround time and response time.	[4]
		<u>UNIT-III</u>	
Q.3	Exp	lain the following terms in memory management:-	
	(a)	Fragmentation	[4]
	(b)	Swapping	[4]
	(c)	Paging	[4]
	(d)	Segmentation	[4]
		<u>OR</u>	
Q.3	Wri	te short note on page replacement algorithm.	[16]
		<u>UNIT-IV</u>	,
Q.4	(a)	Write short note on Firewall.	[8]
	(b)	Explain protection domain of access matrix.	[8]
		<u>OR</u>	
Q.4	(a)	Explain the technique of user authentication.	[8]
	(b)	Explain the implementation of Files and Directories management.	[8]
			[o]
[7E4	051]	Page 2 of 3 [1	140]

# <u>UNIT-V</u>

3)5

Q.5	(a)	Write short note on system model.	[6]
	(b)	Explain in detail about the method for deadlock detection.	[6]
	(c)	What are the characteristic of deadlock?	[4]
×		OR OR	
Q.5	Wr	ite about deadlock avoidance algorithm in detail. How does deadlock a	avoidance
	diff	fer from deadlock prevention?	[16]
		•	

Total No of Pages: 3 Roll No. 7E4054 B. Tech. VII Sem. (Back) Exam., Nov. - Dec. - 2017 **Instrumentation Control Engineering** 7EI3 (O) Computer Networks Maximum Marks: 80 Time: 3 Hours Min. Passing Marks: 26 Instructions to Candidates: Attempt any five questions, selecting one question from each unit. All questions carry equal marks. Schematic diagrams must be shown wherever necessary. Any data you feel missing suitably be assumed and stated clearly. Units of quantities used/calculated must be stated clearly. Use of following supporting material is permitted during examination. (Mentioned in form No. 205) 2. <u>NIL</u> 1. NIL **UNIT-I** Q.1 (a) What is a queuing problem? Explain queuing system, transient and steady [8] ·state. Express mathematical model for M/M/1 Queues. [8] OR [8] Q.1 (a) Explain characteristics and classification of queuing models. (b) Explain the following terms briefly in context to Queuing -[4] (i) Birth - death process [4] (ii) Service discipline [100] Page 1 of 3 [7E4054]

# UNIT-II

Q.2	(a)	A channel has a bit rate of 4 kbps and a propagation delay of 20msec. For	what
		range of frame sizes does stop-and-wait give an efficiency of at least 50 %?	[8]
	(b)	Draw OSI architecture and explain briefly.	[8]
		OR	
Q.2	(a)	Draw and explain the frame structure of HDLC.	[8]
	(b)	Write a short note on:	
		(i) Sliding window protocol	[4]
		(ii) Stop and wait protocol	[4]
		<u>UNIT-III</u>	
Q.3	(a)	Measurement of a slotted ALOHA channel with an infinite number of users s	how
		that 10 percent of the slots are idle.	[8]
		(i) What is the throughput?	
		(ii) Is the channel under loaded or over loaded?	
	(b)	Discuss following terms:	
		(i) Token Ring	[4]
		(ii) FDDI	[4]
		<u>OR</u>	
Q.3	(a)	Consider building a CSMA/CD network running at 1Gbps over a 1-km of	able
		with no repeaters. The signal speed in the cable is 200,000 km/sec. What is	s the
[754	0541	minimum frame size?	[8]
[7E4	054]	Page 2 of 3 [10	0]

	(b)	Discuss following terms:	
		(i) Bridges	[4]
		(ii) Routers and gateways	[4]
		<u>UNIT-IV</u>	
Q.4	(a)	What is difference between IPv6 and IPv4?	[8]
	(b)	Describe OSPF in detail.	[8]
		<u>OR</u>	
Q.4	(a)	What is congestion in Computer Networks? Write general principles	of
		congestion control.	[8]
	(b)	What are the basic design issues of Network Layers? Also explain the serv	ices
		provided by the network layer to the transport layer.	[8]
		<u>UNIT-V</u>	
Q.5	(a)	What is difference between Virtual Path Identifier (VPI) and Virtual Cha	ınnel
		Identifier (VCI)?	[6]
	(b)	Draw and explain ATM protocol architecture.	[10]
		<u>OR</u>	
Q.5	(a)	Discuss X.25 and Frame Relay.	[6]
	(b)	Draw and explain ISDN system architecture. Also explain all channel of I	SDN
		system.	[10]
[7E	(4054	Page 3 of 3 [10	00]

Roll No. Total No of Pages: 3 7E4055 B. Tech. VII Sem. (Back) Exam., Nov. - Dec. - 2017 Biomedical Engineering 7BM6.3 Fiber Optic Instrumentation EIC, BM Time: 3 Hours Maximum Marks: 80 Min. Passing Marks: 26 Instructions to Candidates: Attempt any five questions, selecting one question from each unit. All questions carry equal marks. Schematic diagrams must be shown wherever necessary. Any data you feel missing suitably be assumed and stated clearly. Units of quantities used/calculated must be stated clearly. Use of following supporting material is permitted during examination. (Mentioned in form No. 205) 1. NIL 2. NIL **UNIT-I** Q.1 (a) A glass clad fibre is made with core glass of refractive index 1.5 and the cladding is doped to give a fractional index difference of 0.0005. Find-(i) The cladding index (ii) The critical internal refection angle (iii) The external critical acceptance (iv) The numerical aperture [8] (b) Differentiate between single mode and multimode fibre. [8] OR A single mode fibre is made with a core diameter of 10 µm and is coupled to a Q.1 (a) laser diode that produces 1.3 µm light. Its core glass has a refractive index of 1.55-[8] Find the maximum value required for the normalized index difference. (ii) Find the refractive index required for the cladding glass (iii) Find the fiber acceptance angle.

Page 1 of 3

[100]

[7E4055]

(b) Explain mode theory for circular waveguides. Discuss the different types of

		modes	8]
		<u>UNIT-II</u>	
Q.2	(a)	What are the types of optical correctors? What are the requirements of a good	od
		optical fibre connector design? Explain connector return loss.	8]
	(b)	Explain quantum efficiency and LED power. Also deduce the expression f	or
			8]
		<u>OR</u>	
Q.2	(a)	Explain LED emission pattern and characteristics of LED's.	8]
	(b)	Explain optical coupler, optical splitter and optical combiner with suitab	ole
		diagrams.	[8]
		UNIT-III	
Q.3	(a)	Explain different processes of photo detectors. Discuss different types of option	cal
		detectors. What are the requirements of photo detector for good performance? [	[8]
	(b)	A pin photodiode has a quantum efficiency of 50% at a wavelength of 0.9 $\mu$	m.
		Calculate-	[8]
		(i) its responsively at 0.9 μm.	
		(ii) the received optical power if the mean photo-currents is 10 <sup>-6</sup> A, and	
		(iii) The corresponding number of received photons at this wavelength.	
		<u>OR</u>	
Q.3	(a)	Discuss different noise source in photodiodes.	[8]
	(b)	An InGaAs pin photodiode has the following parameters in wavelength of 11	00
		nm: $I_D = 4$ nA, $\eta = 0.90$ , $R_L = 1000 \Omega$ and the surface leakage current	is
		negligible. The incident optical power is 300nw and the receiver bandwidth	is
		20MHz. Find the value of primary photocurrent, quantum noise current, da	ark
		current and thermal noise current.	[8]
		<u>UNIT-IV</u>	
Q.4	(a)	The photoelectric coefficient and the refractive index for silica are 0.286 and 1	.40
		respectively. Silica has an isothermal compressibility of 7×10 <sup>-11</sup> m <sup>2</sup> N <sup>-1</sup> and	
		estimated fictive temperature of 1400K. Determine the theoretical attenuation	
		decibels per kilometer due to the fundamental Rayleigh's scattering in silica	
[7E4	1055]	Page 2 of 3 [100]	

		optical wavelengths of 0.63 and 1.55 $\mu m$ . Boltzmann's constant is
		$1.38 \times 10^{-23} \text{ JK}^{-1}$ . [8]
	(b)	What is Bending Loss? Explain Intermodal Dispersion and Intramodal
		Dispersion. [8]
		OR
Q.4	(a)	Consider a 30km long optical fibre that has an attenuation of o.8 dB/km at
		1300nm. If 200 µw of optical power is launched into the fibre, find the optical
		output power. [8]
	(b)	Explain absorption losses. Discuss intrinsic absorption and extrinsic absorption
		loss. [8]
		UNIT-V
Q.5	(a)	Explain vertical cavity surface emitting LASERs. Discuss the characteristics of
		the emitted light by LASER diodes. [8]
	(b)	Compute the gain constant and the threshold concentration for a GaAs Laser if
		the absorption coefficient is 10cm <sup>-1</sup> and the length of the cavity is 500 µm. Light
		is emitted at 0.84 $\mu$ m, the bandwidth of the emission peak is 1.5×10 <sup>13</sup> Hz, the
		spontaneous decay time is $10n$ sec, and the index of refraction is $n = 3.6$ . The
		mirrors on either and of the laser are formed by a cleaned GaAs surface. [8]
		OR
Q.5	(a)	Discuss how semiconductor LASER differs from other LASER in several
		aspects. Explain relationship between spontaneous and stimulated emission
	56	probabilities. [8]
•	(b)	What is threshold condition in LASER diode in terms of gain loss relationship?
		How can you measure the threshold current of LASER diode? [8]

Total No of Pages: 2 Roll No. 7E4056 B. Tech. VII Sem. (Back) Exam., Nov. - Dec. - 2017 **Electronic Instrumentation & Control Engineering** 7EI5 (O) Industrial Measurements Maximum Marks: 80 Time: 3 Hours Min. Passing Marks: 26 Instructions to Candidates: Attempt any five questions, selecting one question from each unit. All questions carry equal marks. Schematic diagrams must be shown wherever necessary. Any data you feel missing suitably be assumed and stated clearly. Units of quantities used/calculated must be stated clearly. Use of following supporting material is permitted during examination. (Mentioned in form No. 205) 2. NIL 1. NIL **UNIT-I** Explain the principle of RTD with suitable diagram. [8] Q.1 (a) [8] Explain the principle of Radiation Pyrometer. OR Explain thermocouple and also explain its advantages and disadvantages. [8] Q.1 (a) [8] Explain the principle of Bimetallic Thermometer. **UNIT-II** Write short notes on:-O.2 (a) [4] Diaphragms (i) [4] (ii) Bellows (b) Explain the working of capacitive transducer and how it is used for measurement [8] of pressure. [140] Page 1 of 2 [7E4056]

# <u>OR</u>

Q.2	(a)	Explain Piezoelectric transducer. Also explain property of	piezoelectric
		crystal.	[8]
	(b)	Explain manometer and its type with suitable diagram.	[8]
		<u>UNIT-III</u>	
Q.3	(a)	Explain the working of Electro-magnetic flow meter.	[8]
	(b)	Write short notes on:-	
		(i) Pitot Tube	[4]
		(ii) Rota meter	[4]
		<u>OR</u>	
Q.3	(a)	Explain the principle of mass flow meter.	[8]
	(b)	Explain Ultrasonic Flow Meter.	[8]
		<u>UNIT-IV</u>	
Q.4	(a)	Explain capacitance transducer for measurement of level of Nor	n-Conducting
		liquid.	[8]
	(b)	Explain Radiation Densitometer.	[8]
		<u>OR</u>	
Q.4	(a)	Explain the working of Hydrometer for density measurement.	[8]
	(b)	Explain ultrasonic densitometer.	[8]
		<u>UNIT-V</u>	
Q.5	(a)	Derive the expression for Gauge factor for electrical strain Gauge.	[8]
	(b)	Explain strain Gauge calibration.	[8]
		<u>OR</u>	
Q.5	Writ	te short notes on:-	
	(a)	Rosette Gauge	[8]
	(b)	Wire and Foil Strain Gauge	[8]

[7E4056]

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Roll No.

Total No of Pages: 2

#### 7E7073

B. Tech. VII Sem. (Main/Back) Exam, Nov – Dec. 2017 **Electronic Instrumentation & Control Engineering** 7EI4A Analytical & Environmental Instrumentation

Time: 3 Hours

Maximum Marks: 80

Min. Passing Marks: 26

Instructions to Candidates:

Attempt any five questions, selecting one question from each unit. All questions carry equal marks. Schematic diagrams must be shown wherever necessary. Any data you feel missing suitably be assumed and stated clearly.

Units of quantities used/calculated must be stated clearly.

Use of following supporting material is permitted during examination. (Mentioned in form No. 205)

1. NIL

2. NIL

## **UNIT-I**

- Explain the "Time of flight type Mass" spectrometer with the merits and Q.1 (a) demerits. [8]
  - (b) Explain the applications, advantages and disadvantages of X-ray spectroscopy.[8]

#### OR

- How will you analysis with the help of photo acoustic spectroscopy. Explain in Q.1 (a) brief. [8]
  - [8] (b) What is Beer – Lambert's Law? Explain the various terms involved in it.

## UNIT-II

- Q.2 (a) Explain the principle of infra red gas analyser with suitable examples. How hydrocarbons are detected by infra - red gas analyser. [8]
  - (b) What is chemiluminescence? How nitric oxide (NO) is measured with Carbon [8] monoxide laser?

[300]

		OR	
Q.2	(a)	Explain the construction and working of ultraviolet absorption gas analyzers.	[8]
	(b)	Discuss about the utility of oxygen analyzers in process Industry. Explain	the
		working of paramagnetic oxygen analyzers.	[8]
		UNIT-III	
Q.3	(a)	What are the basic requirements of the detectors used in	the
		gas chromatography?	[8]
	(b)	What is the importance of electron capture detector? Explain its working	
		advantages and disadvantages.	[8]
		OR	[°]
Q.3	(a)	What do you mean by "chromatography". Explain thin layer chromatogra	phy
		with neat sketch.	[8]
	(b)	Give the block diagram of liquid chromatography and explain its various parts	s.[8]
		UNIT-IV	
Q.4	(a)	How carbon monoxide (CO) and sulphur dioxide SO <sub>2</sub> are measured in air.	[8]
	(b)	Explain the visible emission monitoring system with specified applications.	[8]
		OR	
Q.4	(a)	What are the air pollutants? How they are added in air? How solid suspen	ded
		matters are measured in air.	[8]
	(b)	Explain the construction and working of smoke monitoring systems.	[8]
		UNIT-V	
Q.5	Wri	te short notes on the following-	
	(a)	Silica analyzers	[8]
	(b)	pH meters	[8]
		<u>OR</u>	
Q.5	Writ	te short notes on the following- Conductivity meters	
	(b)	Ammonia analyzers	[8] [8]
	(F)		[0]

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		<u>OR</u>		
Q.2	Explain the following:-			
	(a)	Recent trends and future directions of learning Algorithm.	[8]	
	(b)	Feed forward methods of learning Algorithm.	[8]	
		<u>UNIT-III</u>		
Q.3	(a)	What is fuzzy set? Explain degree or membership. How does one re-	epresent a	
		fuzzy set in a computer?	[8]	
	(b)	What are membership functions? Explain with the help of an example.	[8]	
		<u>OR</u>		
Q.3	Exp	lain the following:-		
	(a)	Membership value assignment	[8]	
	(b)	Uncertainty in information	[8]	
		<u>UNIT-IV</u>		
Q.4	(a)	What are the various methods of defuzzification? Discuss sampling r	nethod of	
		defuzzification.	[8]	
	(b)	Explain different Graphical techniques of reference.	[8]	
		<u>OR</u>		
Q.4	Explain the following:-			
	(a)	Aggregation of fuzzy rules	[8]	
	(b)	Decomposition of compound rules	. [8]	
		<u>UNIT-V</u>		
Q.5	Explain the following:-			
	(a)	Industrial Application of Fuzzy Control System	[8]	
	(b)	General FLC Model	[8]	
		<u>OR</u>		
Q.5	Exp	lain simple fuzzy logic controller using suitable diagram.	[16]	
[7E4	001]	Page 2 of 2	[100]	

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[100]

Total No of Pages: 4 Roll No. 7E7071 B. Tech. VII Sem. (Main/Back) Exam., Nov. - Dec. - 2017 **Electronic Instrumentation & Control Engineering** 7EI1A Neural Networks and Fuzzy Logic Control Time: 3 Hours Maximum Marks: 80 Min. Passing Marks: 26 Instructions to Candidates: Attempt any five questions, selecting one question from each unit. All questions carry equal marks. Schematic diagrams must be shown wherever necessary. Any data you feel missing suitably be assumed and stated clearly. Units of quantities used/calculated must be stated clearly. Use of following supporting material is permitted during examination. (Mentioned in form No. 205) 1. NIL 2. NIL UNIT-I Q.1 (a) Explain comparison between Artificial and Biological Neural Networks. [6] (b) Develop a perceptron for AND function with binary inputs and bipolar targets without bias up to 2 epochs. (take first with (0, 0) & next without (0, 0)). OR Q.1 (a) Realize the XOR function using McCulloch Pitts neuron. [8] Using the Hebb rule, find the weight required to perform the following (b) (i) classifications. Vectors (1 1 1 1) & (-1 1 -1 -1) are members of class (with target value 1); Vectors (1 1 1 -1) & (1 -1 -1 1) are not members of class

(ii) Using each of the training X vectors as input, test the response of the net.[4]

[4]

(with target value -1)

#### **UNIT-II**

Q.2 Find the new weights when the network is presented the input pattern  $[0.6 \ 0.8 \ 0]$  and target output is 0.9. Use learning rate  $\alpha = 0.3$  and use binary sigmoid activation function.

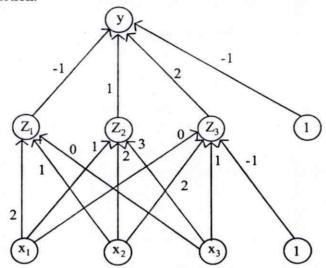


Fig. A Back propagation net

#### <u>OR</u>

Q.2 (a) Explain adaline as a linear adoptive filter.

- [8]
- (b) Explain the last mean square (Widrow Hoff) learning algorithm.

#### [8]

## **UNIT-III**

Q.3 In soil mechanics the stability & strength of a soil is largely dependent on how well a soil is gradiated & how well a soil is compacted. Suppose we have a fuzzy set defined on a universe of soil gradations, Poor, Moderate & Uniform as  $X = \{x_1, x_2, x_3\}$  & a

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fuzzy set defined on a universe of three levels of compaction, low, medium & high as  $y = \{y_1, y_2, y_3\}$ . We then define a "Poorly gradiated soil" as-

$$^{A}_{N} = \left\{ \frac{0.9}{x_1} + \frac{0.4}{x_2} + \frac{0.0}{x_3} \right\}$$

and a "well compacted soil" as

(a) Find the relation,  $R = A \times B$  using a Cartesian product. Let C be another fuzzy set which is a "sufficiently gradated soil" [8]

$$\overset{\text{C}}{\mathsf{N}} = \left\{ \frac{0.3}{\mathsf{x}_1} + \frac{1.0}{\mathsf{x}_2} + \frac{0.2}{\mathsf{x}_0} \right\}$$

(b) Using min-max composition find  $\stackrel{S}{\sim} = \stackrel{C}{\sim} 0 \stackrel{R}{\sim}$ . [8]

#### <u>OR</u>

Q.3 (a) If two fuzzy sets namely:

$$\mathbf{D}_{1} = \left\{ \frac{1}{1.0} + \frac{0.75}{1.5} + \frac{0.3}{2.0} + \frac{0.15}{2.5} + \frac{0}{3.0} \right\}$$

$$D_{\mathcal{C}}^{2} = \left\{ \frac{1}{1.0} + \frac{0.6}{1.5} + \frac{0.2}{2.0} + \frac{0.1}{2.5} + \frac{0.0}{3.0} \right\}$$

Find

(i) 
$$\bigvee_{N}^{D_1} \cup \bigvee_{N}^{D_2}$$

(ii) 
$$\bigvee_{N=1}^{D_1} \cap \bigvee_{N=1}^{D_2}$$

(iii) 
$$\overline{\overline{D}}_1$$

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[320]

[10]

		(iv) $\overline{D_2}$	
		$(v)  \stackrel{D_1}{\bowtie} / \stackrel{D_2}{\bowtie}$	
		(vi) $\overline{D_1 \cap D_2}$ $V$	
	(b)	Explain features of membership function.	[6]
		<u>UNIT-IV</u>	
Q.4	(a)	For the inference rule	[8]
		$[(A \to B) \land (B \to C)] \to (A \to C),$	
		prove that the rule is a tautology.	
	(b)	Explain aggregation of fuzzy sets.	[8]
		OR	
Q.4	(a)	Explain natural language in fuzzy logic.	[8]
	(b)	Explain Linguistic Hedges in fuzzy logic.	[8]
		<u>UNIT-V</u>	
Q.5	Exp	lain the three - tank MIMO problem with fuzzy logic control.	[16]
		OR	
Q.5	Exp	lain fuzzy statistical process control with example.	[16]